

*#6/Janet B
Gard*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant(s): Halahan, Patrick B.; Siniaguine, Oleg

Assignee: Tru-Si Technologies, Inc.

Title: Semiconductor Structures Having Multiple Conductive Layers In An Opening, And Methods For Fabricating Same

Application No.: 09/941,447 Filing Date: 08/28/2001

Examiner: Thomas, Toniae M. Group Art Unit: 2822

Docket No.: M-9999-1D US

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AMENDMENT

Sir:

Responsive to the Office Action mailed 5 June 2002, please amend the above patent application as follows:

09/06/2002 GGBREGI 00000026 192386 09941447

01 FC:103 828.00 CH

IN THE TITLE

Before "SEMICONDUCTOR STRUCTURES" insert --FABRICATION OF--;

delete ", AND METHODS FOR FABRICATING SAME".

IN THE SPECIFICATION

Page 1, amend the paragraph beginning at line 14 to read

--According to some aspects of the invention, a circuit manufacturing method comprises:

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